

isc N-Channel MOSFET Transistor

IPP90R800C3

• FEATURES

- With TO-220 packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

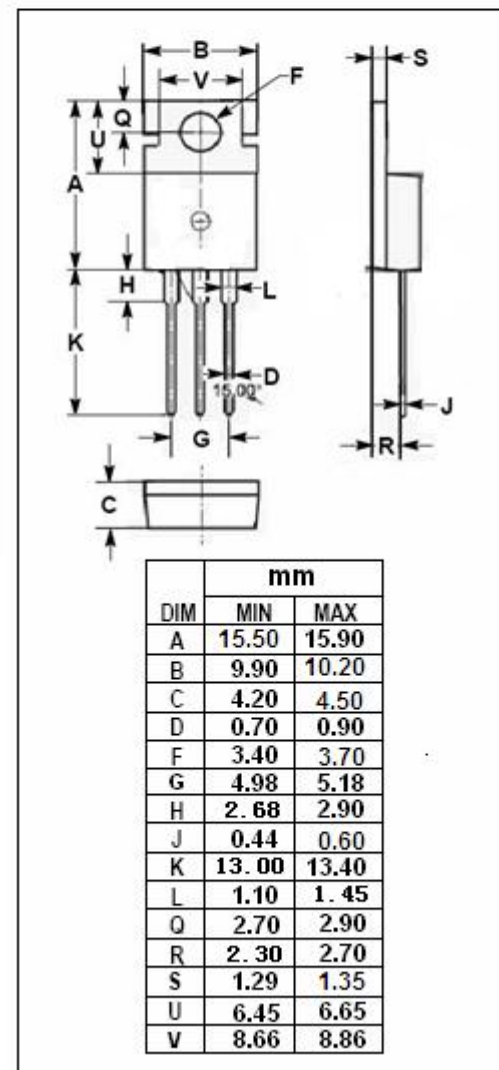
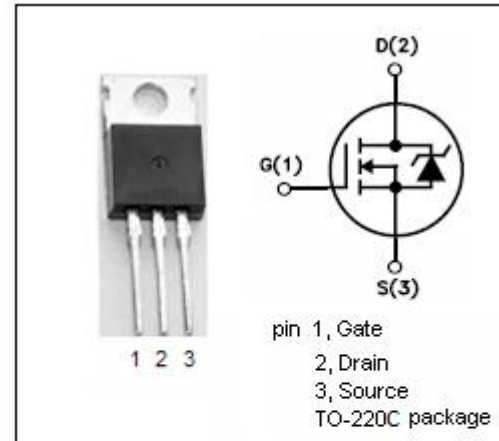
- Power supply
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	900	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous; @T _c =25°C T _c =100°C	6.9 4.4	A
I _{DM}	Drain Current-Single Pulsed	15	A
P _D	Total Dissipation	104	W
T _j	Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	1.2	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	62	°C/W



isc N-Channel MOSFET Transistor**IPP90R800C3****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=0.25mA$	900			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.46mA$	2.5		3.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=4.1A$		620	800	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=900V; V_{GS}=0V$			1	μA
V_{SDF}	Diode forward voltage	$I_{SD}=4.1A, V_{GS}=0V$		0.8	1.2	V